

# DATA SHEET

## **PDTA144E series**

PNP resistor-equipped transistors;

R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

Product specification  
Supersedes data of 2003 Apr 10

2004 Aug 05

## PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

## PDTA144E series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	–50	V
I <sub>O</sub>	output current (DC)	–	–100	mA
R1	bias resistor	47	–	k $\Omega$
R2	bias resistor	47	–	k $\Omega$

### DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA144EE	SOT416	SC-75	07	PDTC144EE
PDTA144EEF	SOT490	SC-89	07	PDTC144EEF
PDTA144EK	SOT346	SC-59	07	PDTC144EK
PDTA144EM	SOT883	SC-101	DR	PDTC144EM
PDTA144ES	SOT54 (TO-92)	SC-43	TA144E	PDTC144ES
PDTA144ET	SOT23	–	*07 <sup>(1)</sup>	PDTC144ET
PDTA144EU	SOT323	SC-70	*07 <sup>(1)</sup>	PDTC144EU

### Note

1. \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

PNP resistor-equipped transistors;  
 R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA144ES		1 2 3	base collector emitter
PDTA144EE PDTA144EEF PDTA144EK PDTA144ET PDTA144EU		1 2 3	base emitter collector
PDTA144EM		1 2 3	base emitter collector

PNP resistor-equipped transistors;  
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## PDTA144E series

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–10	V
V <sub>I</sub>	input voltage positive negative		–	+10	V
			–	–40	V
I <sub>O</sub>	output current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
SOT883	notes 2 and 3	–	250	mW	
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
SOT883	notes 2 and 3	500	K/W	

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

PNP resistor-equipped transistors;  
 $R1 = 47 \text{ k}\Omega$ ,  $R2 = 47 \text{ k}\Omega$

PDTA144E series

### CHARACTERISTICS

$T_{\text{amb}} = 25 \text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{\text{CBO}}$	collector-base cut-off current	$V_{\text{CB}} = -50 \text{ V}$ ; $I_{\text{E}} = 0$	–	–	–100	nA
$I_{\text{CEO}}$	collector-emitter cut-off current	$V_{\text{CE}} = -30 \text{ V}$ ; $I_{\text{B}} = 0$	–	–	–1	$\mu\text{A}$
		$V_{\text{CE}} = -30 \text{ V}$ ; $I_{\text{B}} = 0$ ; $T_{\text{j}} = 150 \text{ }^\circ\text{C}$	–	–	–50	$\mu\text{A}$
$I_{\text{EBO}}$	emitter-base cut-off current	$V_{\text{EB}} = -5 \text{ V}$ ; $I_{\text{C}} = 0$	–	–	–90	$\mu\text{A}$
$h_{\text{FE}}$	DC current gain	$V_{\text{CE}} = -5 \text{ V}$ ; $I_{\text{C}} = -5 \text{ mA}$	80	–	–	
$V_{\text{CEsat}}$	collector-emitter saturation voltage	$I_{\text{C}} = -10 \text{ mA}$ ; $I_{\text{B}} = -0.5 \text{ mA}$	–	–	–150	mV
$V_{\text{i(off)}}$	input-off voltage	$I_{\text{C}} = -100 \mu\text{A}$ ; $V_{\text{CE}} = -5 \text{ V}$	–	–1.2	–0.8	V
$V_{\text{i(on)}}$	input-on voltage	$I_{\text{C}} = -2 \text{ mA}$ ; $V_{\text{CE}} = -0.3 \text{ V}$	–3	–1.6	–	V
R1	input resistor		33	47	61	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
$C_{\text{c}}$	collector capacitance	$I_{\text{E}} = i_{\text{e}} = 0$ ; $V_{\text{CB}} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	–	–	3	pF

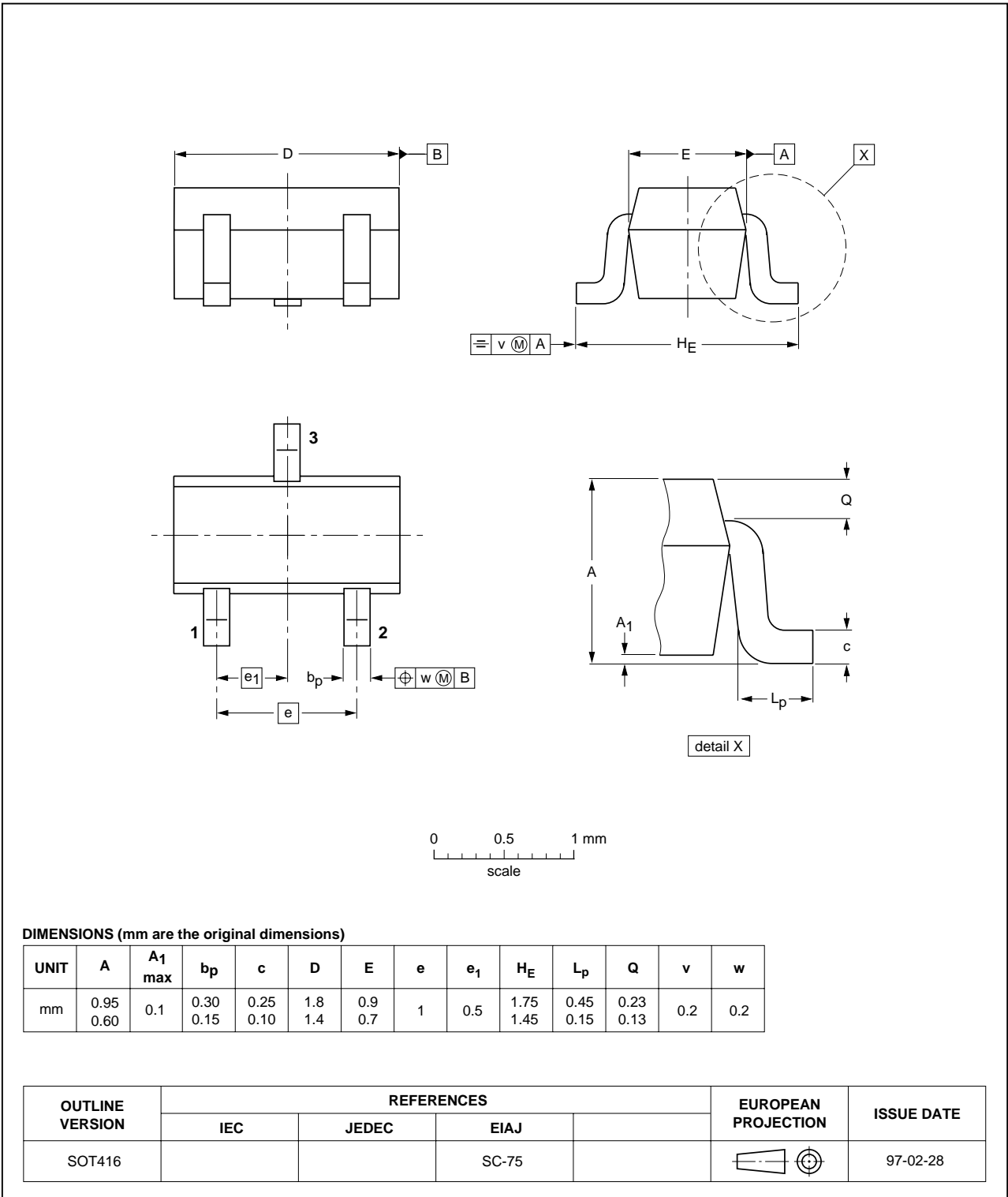
PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416

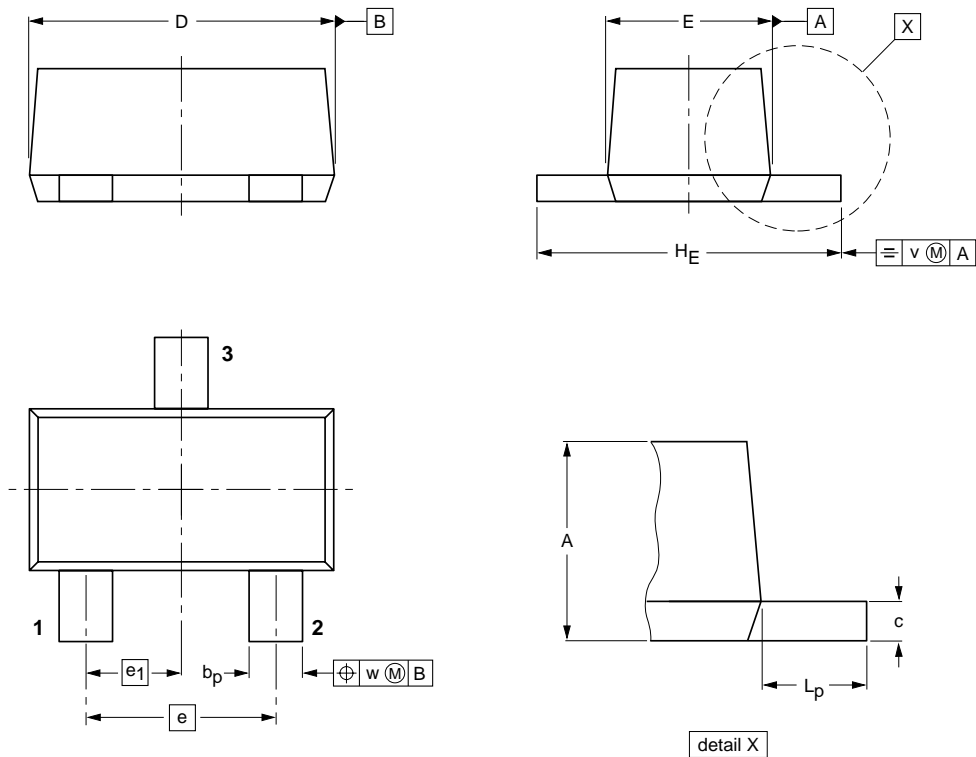


PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic surface mounted package; 3 leads

SOT490



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

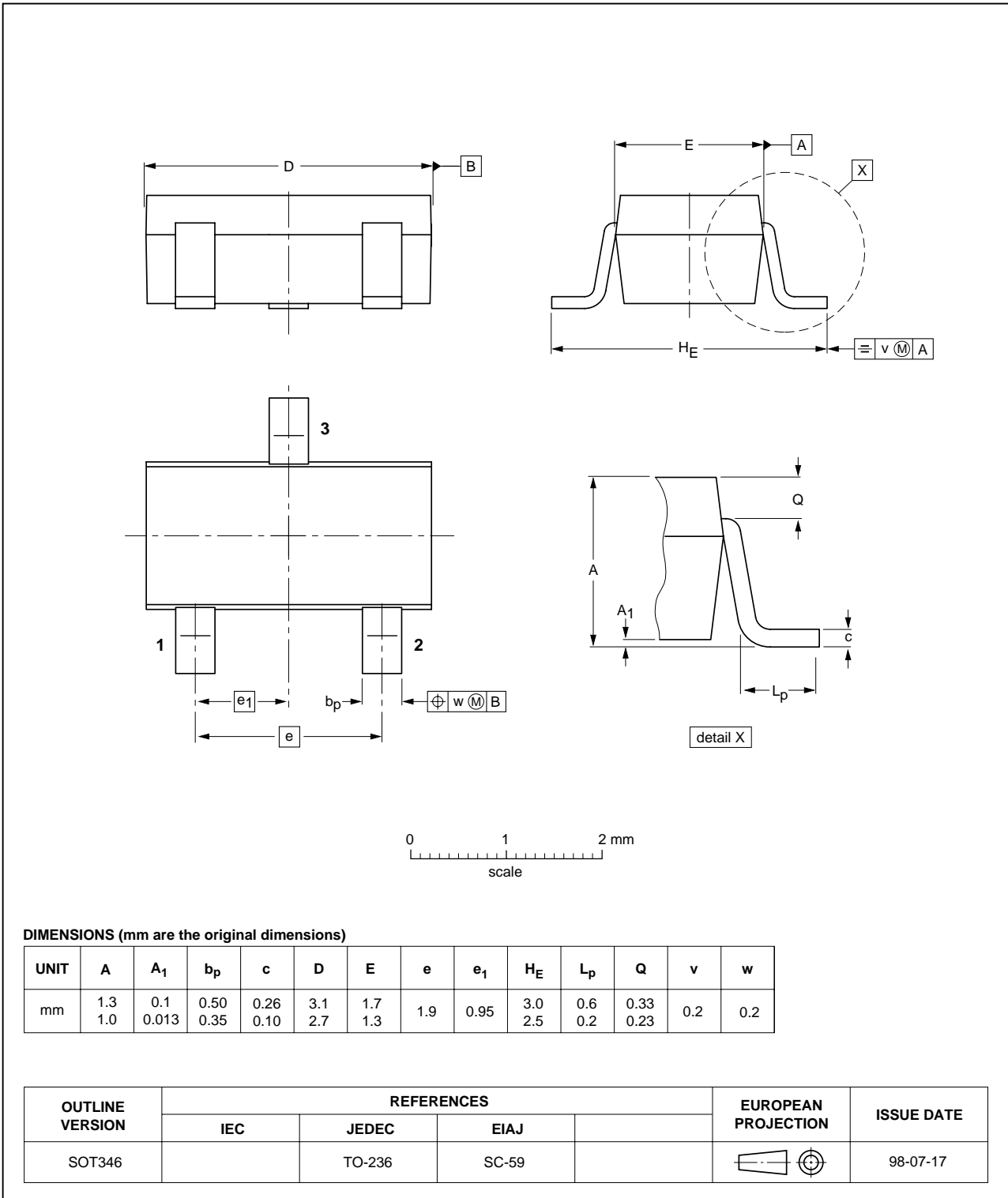
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT490			SC-89		98-10-23

PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic surface mounted package; 3 leads

SOT346



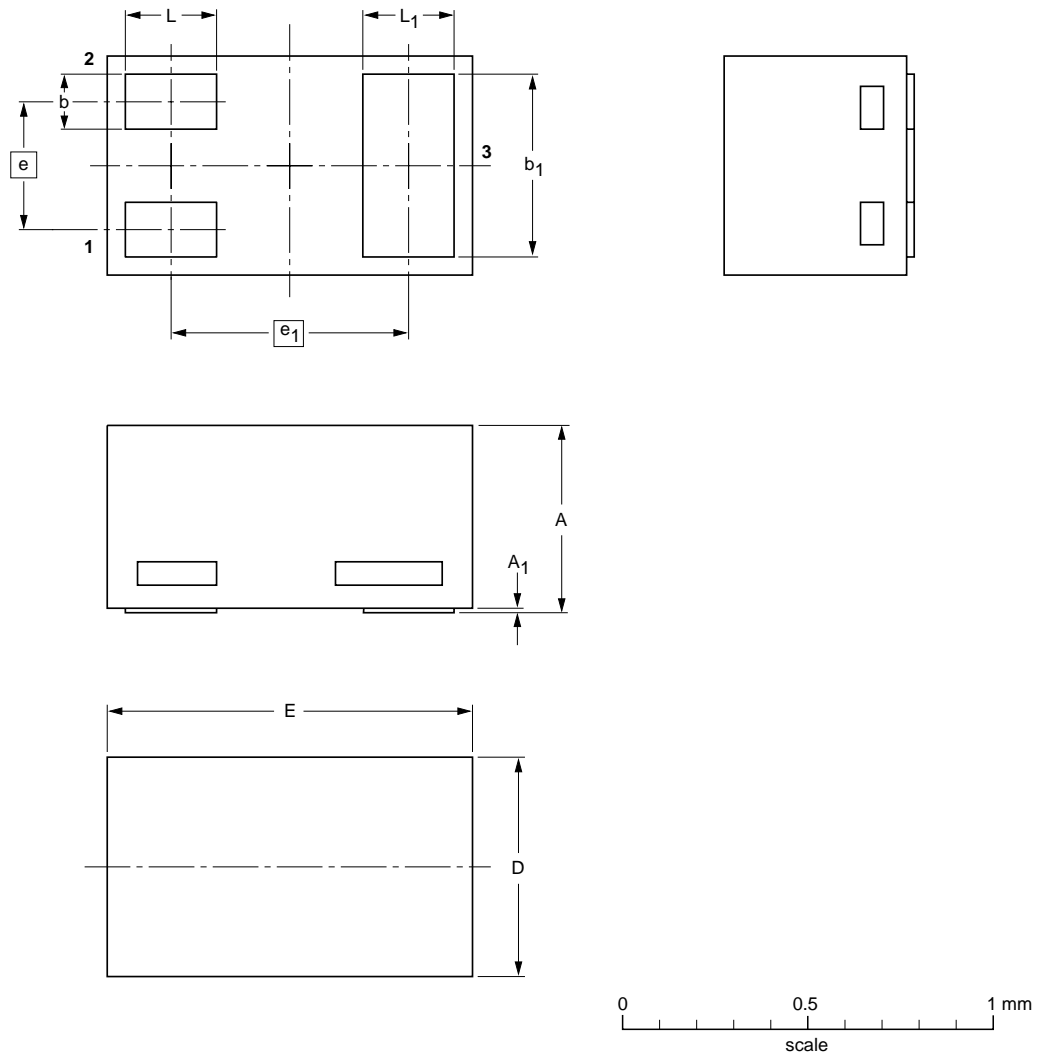


PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A <sup>(1)</sup>	A <sub>1</sub> max.	b	b <sub>1</sub>	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

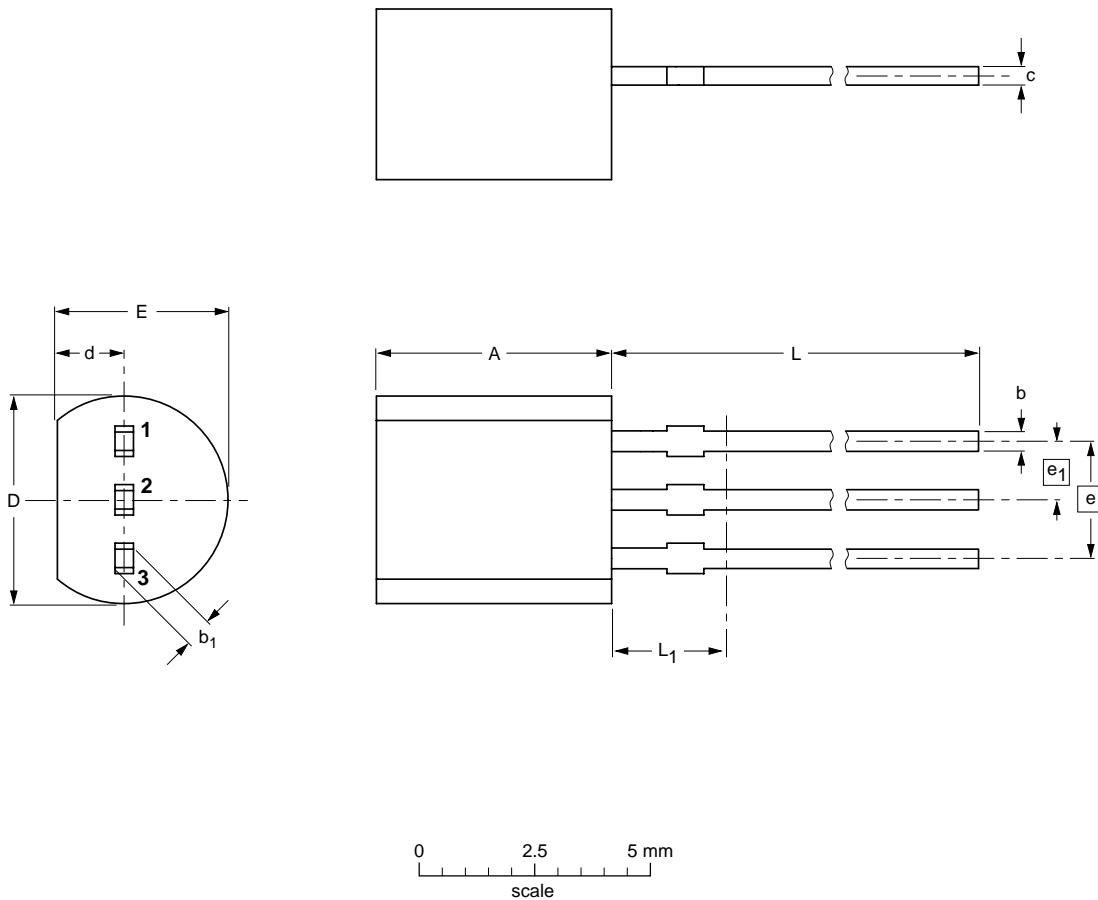
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT883			SC-101		03-02-05 03-04-03

PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

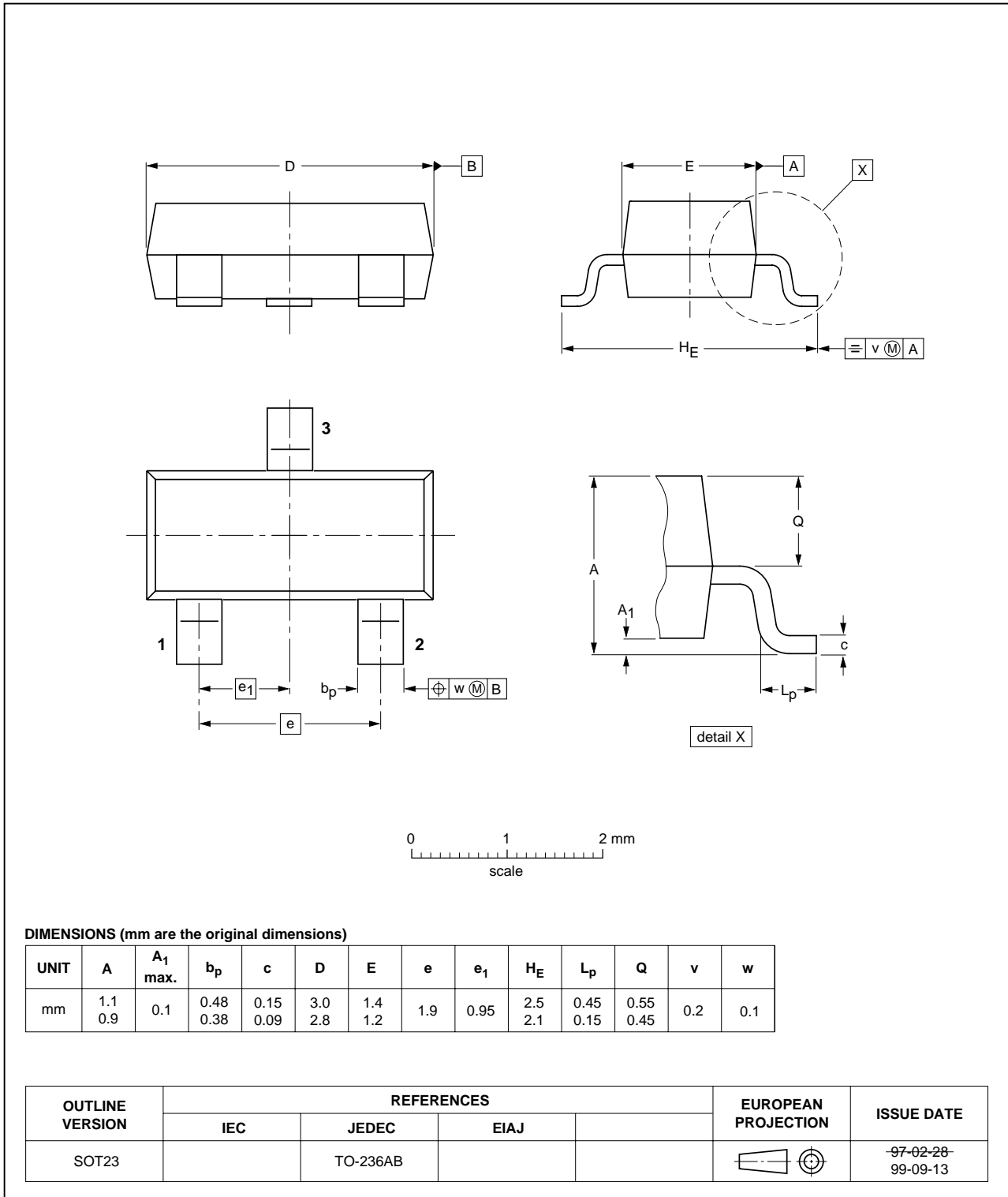
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		-97-02-28 04-06-28

PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic surface mounted package; 3 leads

SOT23

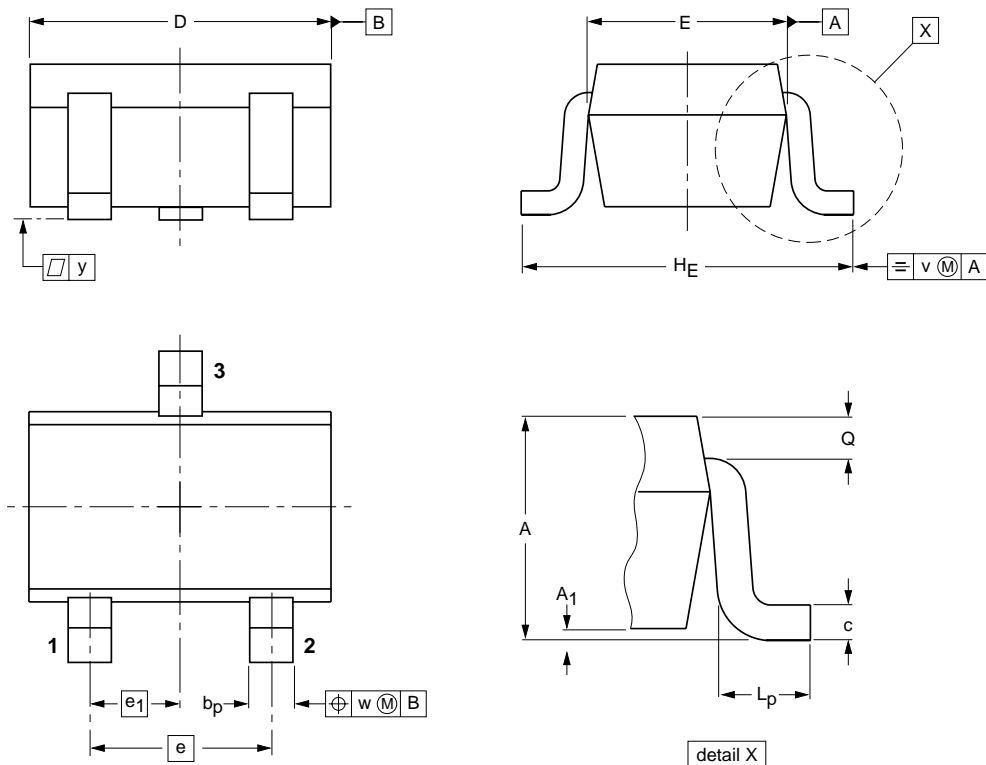


PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

Plastic surface mounted package; 3 leads

SOT323



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

PNP resistor-equipped transistors;  
R1 = 47 kΩ, R2 = 47 kΩ

PDTA144E series

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